

L Number	Hits	Search Text	DB	Time stamp
-	0	(semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI) and LTO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 09:55
-	42	semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 13:42
-	453	semiconductor and SOI and (tungsten or W) and multilayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 13:52
-	41	(semiconductor and SOI and (tungsten or W) and multilayer) and adhesive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 13:54
-	36	((semiconductor and SOI and (tungsten or W) and multilayer) and adhesive) not (semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 13:58
-	2992	((438/622) or (438/582-583) or (438/195) or (438/266) or (438/311) or (438/455) or (438/591) or (438/682-683)).CCLS.	USPAT; US-PGPUB	2002/11/26 14:09
-	213	((438/622) or (438/582-583) or (438/195) or (438/266) or (438/311) or (438/455) or (438/591) or (438/682-683)).CCLS.) and (back with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 14:18
-	1345	((438/455) or (438/406) or (438/459) or (438/479)).CCLS.	USPAT; US-PGPUB	2002/11/26 14:28
-	525	((438/455) or (438/406) or (438/459) or (438/479)).CCLS.) and (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 14:29
-	70	(US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.	USPAT; US-PGPUB	2002/11/26 14:41

	<p>17 ((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and adhesive</p> <p>56 ((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p> <p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	<p>2002/11/26 15:06</p> <p>2002/11/26 15:23</p>
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51	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:28
12	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:30
0			
46	semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:32
		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:32

1	semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:41
1	semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:42
2	semiconductor and ((WSiN) same silane same ammonia)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:45
2518	semiconductor and (nitrid\$6 same tungsten adj silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:48
411	(semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
146	((semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane) and ammonia	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:52
6	semiconductor and (monolayer with (tungsten adj silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
0	(semiconductor and (monolayer with (tungsten adj silicide))) and silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
1	((semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane) and nitrad\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:31
92	semiconductor and (electroplating same electrolessly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:32
54	semiconductor and (electroplating with electrolessly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:35
0	semiconductor and (electroplating with electrolessly with equivalent)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:35
69	semiconductor and SOI and (wafer with bond\$4) and (tungsten or W) and (adhesive or gluing) and passivat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/23 11:24
19	semiconductor and (back with gate) and (wafer with bond\$4) and (tungsten or W) and (adhesive or gluing) and passivat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/23 13:54

1	(back adj gate) and LTO and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 14:36
5	(back adj gate) and LTO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 14:36
2916	semiconductor and (gate and lift adj off)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:49
22	(semiconductor and (gate and lift adj off)) and LTO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:07
2	("6238737").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:20
253	semiconductor and metal and silicide and LTO and (SiN or polysilicon or (amorphous with silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 10:51
2	("6238737").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 14:17
0	((("6238737").PN.) and (glue or gluing or glueing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 14:17
0	((("6238737").PN.) and (glue or gluing or glueing)) and ((amorphous adj silicon) or "a Si" or SiN or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 14:18
0	((("6238737").PN.) and (glue or gluing or glueing)) and ((amorphous adj silicon) or "a Si" or SiN or (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:19
1	(back adj gate) and LTO and ((glue or gluing or glueing or adhesive or bonding) same (SiN or silicon)) and passivat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:21
25	(back adj gate) and (gate adj oxide) and ((glue or gluing or glueing or adhesive or bonding) same (SiN or silicon)) and passivat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:22
2	("5610083").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:31
1472	(438/455-459).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:32

527	((438/455-459).CCLS.) and (refractory or W or Tungsten or Titanium or Ti) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:32
223	((438/455-459).CCLS.) and (refractory or W or Tungsten or Titanium or Ti) and oxide) and (glue or gluing or glueing or adhesive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:33
229396	"11" and (barrier or passivation or silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:33
116	((438/455-459).CCLS.) and (refractory or W or Tungsten or Titanium or Ti) and oxide) and (glue or gluing or glueing or adhesive) and (barrier or passivation or silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:34
58	((438/455-459).CCLS.) and (refractory or W or Tungsten or Titanium or Ti) and oxide) and (glue or gluing or glueing or adhesive) and (barrier or passivation or silicide)) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:47
9	((438/455-459).CCLS.) and (gate.ti.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:40
41	semiconductor and ((tungsten or W) same delamination same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 15:57
2	semiconductor and (back adj gate) and (back adj oxide) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:32
10	semiconductor and (back adj1 gate) and (back adj1 oxide) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:37
112	semiconductor and (double adj gate) and (back adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:38
16	(semiconductor and (double adj gate) and (back adj gate)) and laminat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:45
351	(back adj gate).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:46
348	((back adj gate).ti.) not (semiconductor and (double adj gate) and (back adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:49
140	semiconductor and SOI and gate and (refractory) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:52

-	70	semiconductor and SOI and (gate adj1 oxide) and (refractory) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:53
-	88	semiconductor and SOI and (gate adj1 oxide) and ((refractory) same (barrier or passivation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 20:55
-	27	semiconductor and (SOI adj substrate) and (gate adj1 oxide) and ((refractory) same (barrier or passivation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:15
-	5	semiconductor and (SOI adj substrate) and (gate adj1 oxide) and ((refractory) same (barrier or passivation)) and (second adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:24
-	2	semiconductor and (SOI adj substrate) and (back adj1 gate adj1 oxide) and (refractory or W or Tungsten or Ti or Titanium) and (second adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:29
-	1606	semiconductor and (substrate with lift adj off)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:30
-	561	(semiconductor and (substrate with lift adj off)) and gate\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:30
-	62	((semiconductor and (substrate with lift adj off)) and gate\$1) and (gate adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:32
-	1902	((438/622).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:34
-	678	((438/622).CCLS.) and ((second with substrate) or (handle with wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:34
-	1	((438/622).CCLS.) and ((handle with wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:35
-	2171	semiconductor and (handle with wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:35
-	13	(semiconductor and (handle with wafer)) and (back adj1 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:37
-	494	(semiconductor and (handle with wafer)) and (thin adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:38

-	194	((semiconductor and (handle with wafer)) and (thin adj film)) and (gate with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:52
-	832	semiconductor and (handle adj1 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:52
-	276	(semiconductor and (handle adj1 wafer)) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:52
-	97	((semiconductor and (handle adj1 wafer)) and SOI) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:52
-	65	((((semiconductor and (handle adj1 wafer)) and SOI) and gate) not (((semiconductor and (handle with wafer)) and (thin adj film)) and (gate with oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:53
-	45	(((((semiconductor and (handle adj1 wafer)) and SOI) and gate) not (((semiconductor and (handle with wafer)) and (thin adj film)) and (gate with oxide)))) and (refractive or tungsten or w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/13 21:53
-	14	(back adj gate) and (LTO or (low with temperature with oxide)) and (passivation or adhesive or gluing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:08
-	0	(back adj gate) and (passivation or adhesive or gluing) and ((gluing or adhesi\$5) with (amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:09
-	0	(back adj gate) and (passivation or adhesive or gluing) and (intermediate with (amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:10
-	4	(back adj gate) and (passivation or adhesive or gluing) and ((amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:11
-	0	(back adj gate) and (lift with off) and ((amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:11
-	0	("back-gate") and (lift with off) and ((amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:11
-	3	(metal with back with gate) and ((amorphous or SiN or nitride) with situ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 10:12